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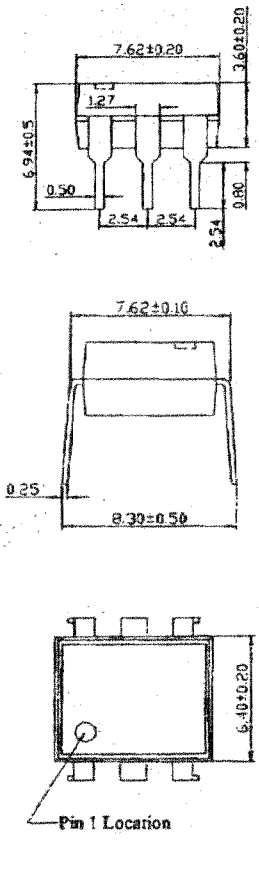
● Max. Ratings (Ta=25℃, RH=45~75%)

Characteristic parameters		symbol	Rated value	unit
input	Forward current	I_F	50	mA
	Reverse voltage	V_R	5	V
	Power dissipation	P_M	75	mW
Output	Off-state repetitive peak forward voltage	V_{DRM}	400	V
	Off-state repetitive peak reverse voltage	V_{RRM}	400	V
	On-state current	$I_{T(RMS)}$	150	mA
	Peak repetitive surge current	I_{TSM}	1	A
	Power dissipation	P_{CM}	150	mW
Operating temp.		T_{OPR}	-30~+100	℃
Storage temp.		T_{STG}	-55~+125	℃
Soldering temp.(10s)		T_{SOL}	260	℃
Total power dissipation		P_{TOT}	230	mW
Isolation voltage (RH≤60%, AC 1min.)		V_{ISO}	5000	V_{rms}

● Outline dimension(Unit:mm)



● Photo-electric Ratings (Ta=25℃)

Parameters		Symb.	Test Conditions		Min.	Typ.	Max.	Unit	Type
Input	Forward voltage	V_F	I_F=10mA			1.2	1.3	V	Cp
	Reverse current	I_R	V_R=5V				10	μA	Cp
Output	Off-state repeated peak forward current	I_{DRM}	V_{DRM}=400V R_{GK}=27kΩ			100	500	nA	Cp
	Off-state repeated peak reverse current	I_{RRM}	V_{RRM}=400V R_{GK}=27kΩ			100	500	nA	Cp
	Off-state voltage critical rise	dv/dt	V_{DRM}=400V_{AC} dv/dt=0.63V_{DRM}/τ			10		V/us	C
	Gate trigger current	I_{GT}	V_{AK}=100V R_{GK}=27kΩ			30	50	μA	Cp
Coupler	LED triggering current	I_{FT}	V_{AK}=6V R_{GK}=27kΩ	HPC981			15	mA	Cp
				HPC982			10		
			V_{AK}=100V R_{GK}=27kΩ	HPC981			11		
				HPC982			8		
	Holding current	I_H				200	500	μA	Cp
	On-state peak voltage	V_{TM}	I_{TM}=100mA			0.9	1.3	V	Cp
	Isolation voltage	Viso	I_{off}≤ 0.3mA AC,60s		5000			V	Cp

Cp: 100% finished parts test parameters;

C: Design control, referance parameters.